

|      |               |      |
|------|---------------|------|
| VRRM | IF ( TC≤135℃) | QC   |
| 650V | 7A            | 13nC |

### Applications:

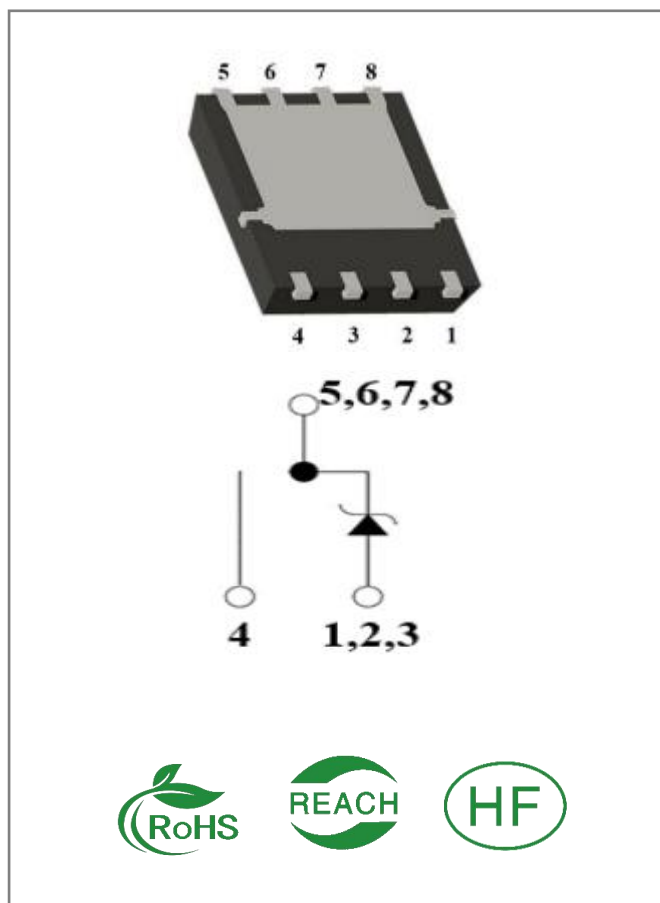
- Switch Mode Power Supplies
- Power Factor Correction
- Motor drive, PV Inverter, Wind Power Station

### Features:

- Zero Reverse Recovery Current
- Zero Forward Recovery Voltage
- Positive Temperature Coefficient on VF
- Temperature-independent Switching
- 175°C Operating Junction Temperature

### Benefits:

- Replace Bipolar with Unipolar Device
- Reduction of Heat Sink Size
- Parallel Devices Without Thermal Runaway
- Essentially No Switching Losses



### Ordering Information

| Part Number | Package | Marking   | Packing   | Qty.     |
|-------------|---------|-----------|-----------|----------|
| RSS04065G   | DFN5*6  | RSS04065G | Tape&reel | 5000 PCS |

**Maximum Ratings** (TJ= 25°C unless otherwise specified)

| Symbol  | Parameter                                  | Value        | Unit | Test Conditions   | Note  |
|---------|--|--------------|------|---|-------|
| VRRM    | Repetitive Peak Reverse Voltage            | 650          | V    | TC = 25°C   |       |
| VRSM    | Surge Peak Reverse Voltage                 | 650          | V    | TC = 25°C   |       |
| VR      | DC Blocking Voltage                        | 650          | V    | TC = 25°C   |       |
| IF      | Forward Current                            | 14<br>7<br>4 | A    | TC ≤ 25°C<br>TC ≤ 135°C<br>TC ≤ 155°C   | Fig.3 |
| IFSM    | Non-Repetitive Forward Surge Current       | 42<br>33     | A    | TC = 25°C, tp = 10ms, Half Sine Wave<br>TC = 110°C, tp = 10ms, Half Sine Wave |       |
| IFRM    | Repetitive Peak Forward Surge Current      | 37           | A    | TC = 25°C, tp = 10ms, Half Sine Wave  |       |
| Ptot    | Power Dissipation                          | 69           | W    | TC = 25°C   | Fig.4 |
| TC      | Maximum Case Temperature                   | 155          | °C   |   |       |
| TJ,TSTG | Operating Junction and Storage Temperature | -55<br>to175 | °C   |   |       |

**Electrical Characteristics** (TJ= 25°C unless otherwise specified)

| Symbol | Parameter                 | Typ.            | Max.     | Unit | Test Conditions  | Note  |
|--------|---------------------------|-----------------|----------|------|--|-------|
| VF     | Forward Voltage           | 1.37<br>1.78    | 1.5<br>- | V    | IF = 4A, TJ = 25°C<br>IF = 4A, TJ = 175°C  | Fig.1 |
| IR     | Reverse Current           | 1.1<br>4.5      | 50<br>-  | μA   | VR = 650V, TJ = 25°C<br>VR = 650V, TJ = 175°C  | Fig.2 |
| C      | Total Capacitance         | 178<br>25<br>24 | /        | pF   | VR = 1V, TJ = 25°C, f = 1MHz<br>VR = 200V, TJ = 25°C, f = 1MHz<br>VR = 400V, TJ = 25°C, f = 1MHz | Fig.5 |
| QC     | Total Capacitive Charge   | 13              | /        | nC   | VR = 400V,   | Fig.6 |
| Ec     | Capacitance Stored Energy | 2.1             |          | uJ   | VR = 400V,   | Fig.7 |

**Thermal Characteristics** (TJ= 25°C unless otherwise specified)

| Symbol | Parameter                                | Typ. | Unit | Note  |
|--------|--|------|------|-------|
| RθJC   | Thermal Resistance from Junction to Case | 2.17 | °C/W | Fig.8 |

## Typical Feature Curve

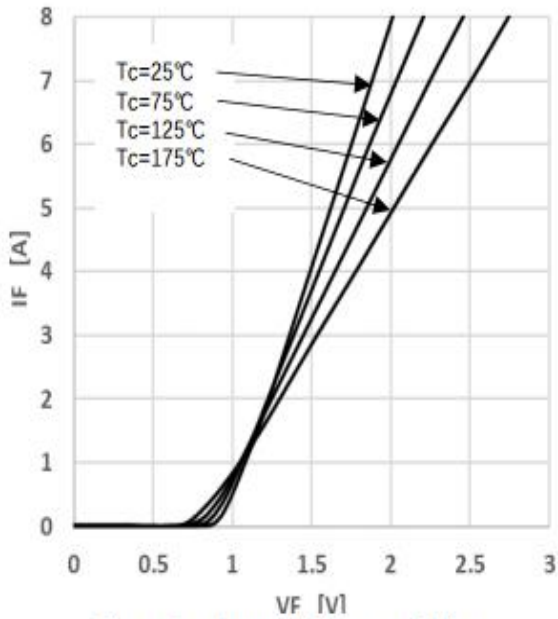


Figure 1 Forward Characteristics

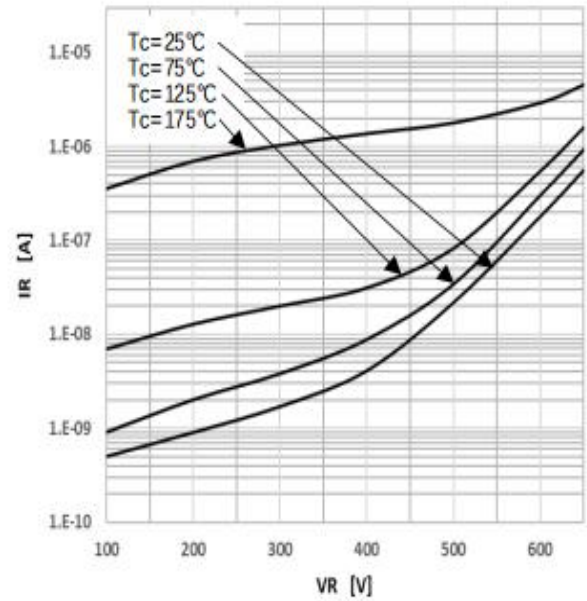


Figure 2 Reverse Characteristics

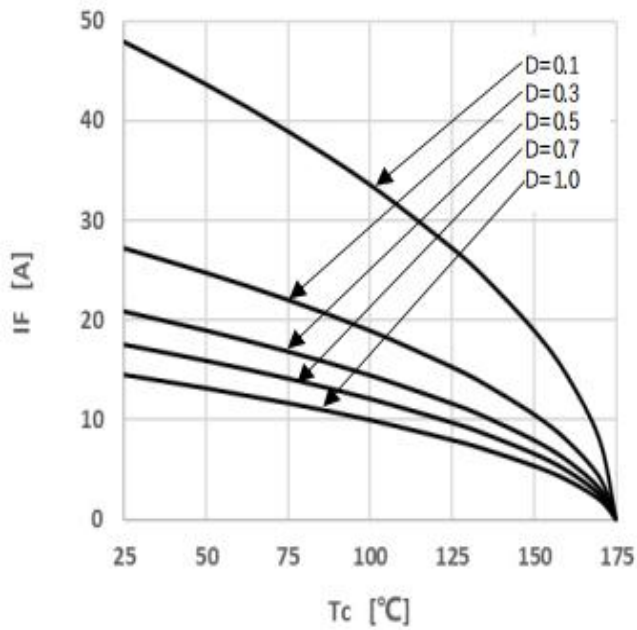


Figure 3 Peak Forward Current Derating

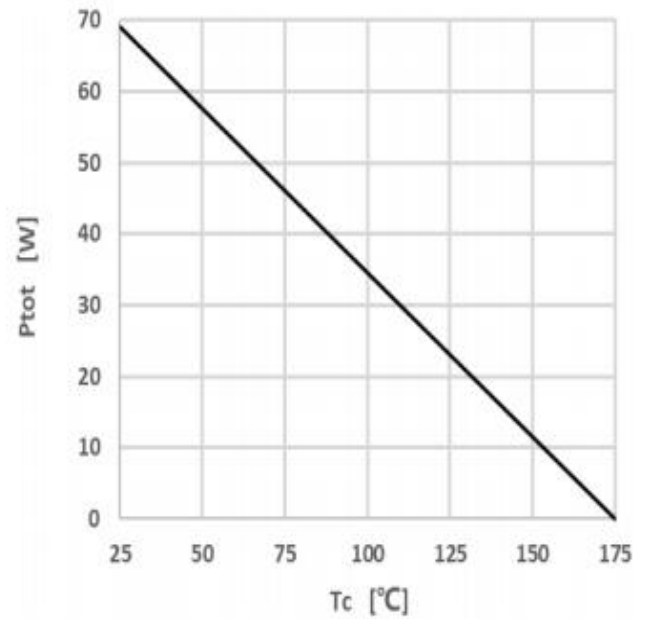


Figure 4 Power Dissipation

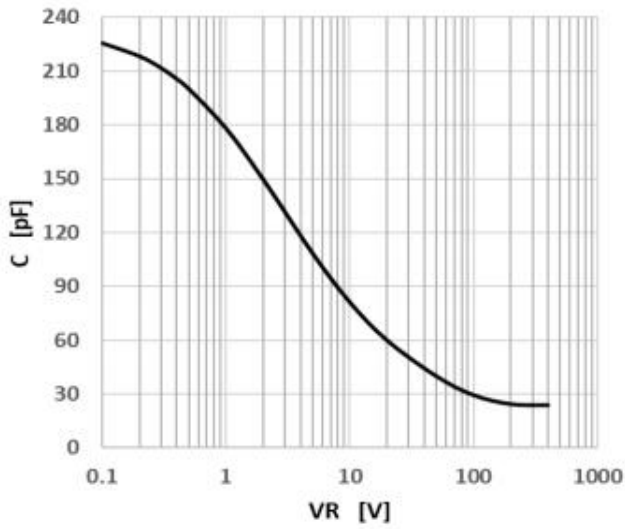


Figure 5 Capacitance vs. Reverse Voltage

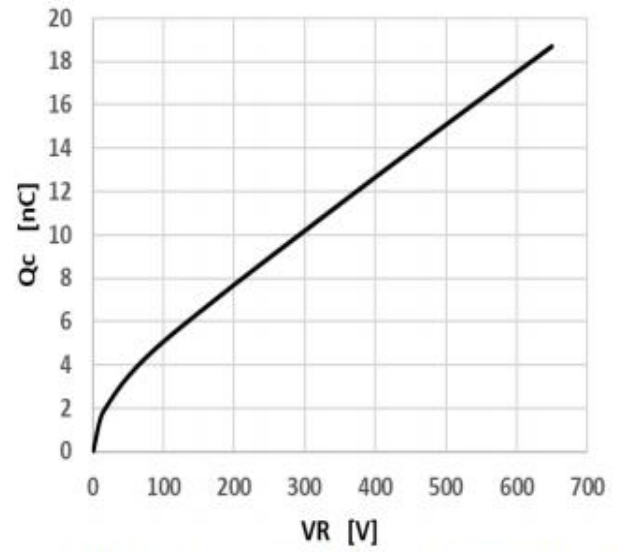


Figure 6 Capacitance Charge vs. Reverse Voltage

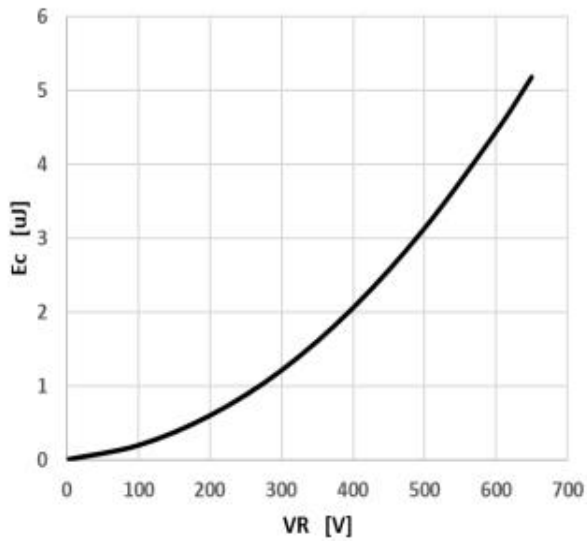


Figure 7 Capacitance Stored Energy

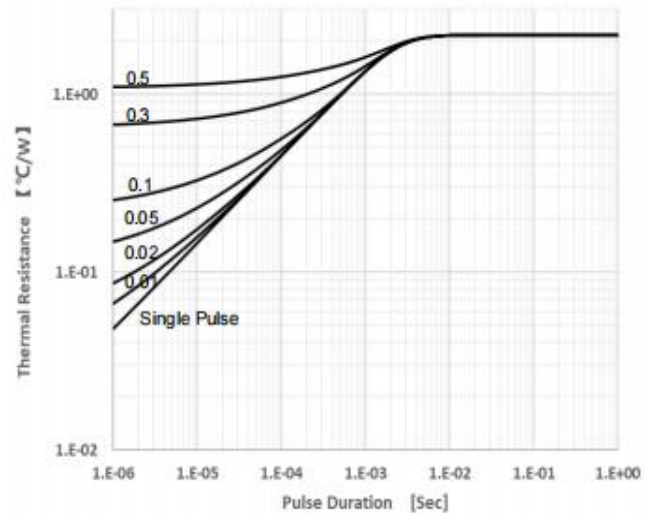
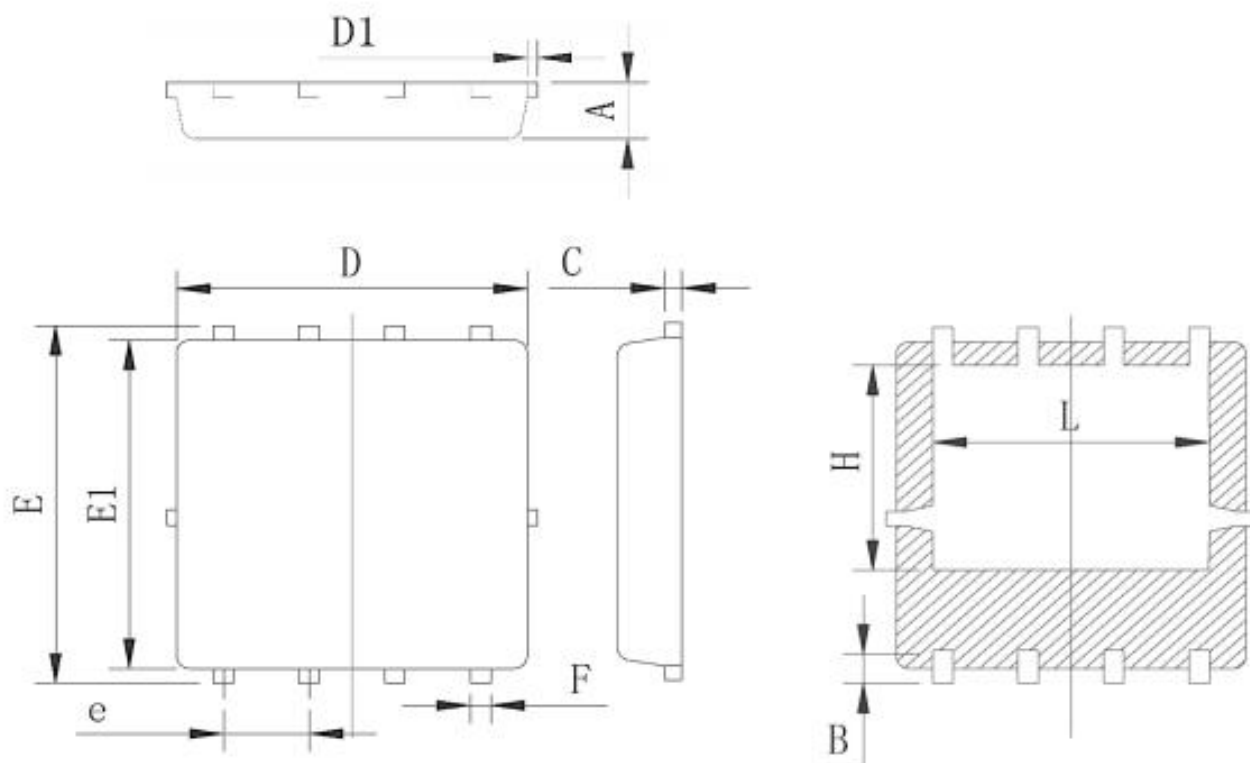


Figure 8 Transient Thermal Impedance

**Package outline drawing(DFN5\*6 Unit: mm )**



| Symbol | Min  | Typ   | Max  |
|--------|------|-------|------|
| A      | 0.90 | 0.95  | 1.00 |
| B      | 0.48 | 0.58  | 0.68 |
| C      | 0.20 | 0.254 | 0.30 |
| D      | 5.00 | 5.20  | 5.40 |
| D1     |      |       | 0.15 |
| E      | 5.90 | 6.05  | 6.20 |
| E1     | 5.40 | 5.55  | 5.70 |
| e      | 1.22 | 1.27  | 1.32 |
| F      | 0.25 | 0.30  | 0.35 |
| H      | 3.27 | 3.47  | 3.67 |
| L      | 3.80 | 4.00  | 4.20 |

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